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Vishay Siliconix

N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^d	Q _g (TYP.)		
40	0.0016 at V _{GS} = 10 V	120	150		
40	0.0019 at $V_{GS} = 4.5 \text{ V}$	120	130		



Ordering Information:

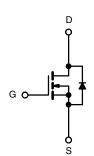
SUM40010EL-GE3 (lead (Pb)-free and halogen-free)

FEATURES

- TrenchFET® power MOSFET
- Maximum 175 °C junction temperature
- Q_{qd}/Q_{qs} ratio < 0.5
- Operable with logic-level gate drive
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



- Power supply
 - Secondary synchronous rectification
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- · Battery management



COMPLIANT

HALOGEN

FREE

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (7	$\Gamma_{\rm C}$ = 25 °C, unless other	erwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	40	V	
Gate-Source Voltage	V _{GS}	± 20	v	
Continuous Duois Coursent /T 150 °C	T _C = 25 °C		120 ^d	
Continuous Drain Current (T _J = 150 °C)	T _C = 70 °C	l _D	120 ^d	
Pulsed Drain Current (t = 100 μs)	I _{DM}	300	A	
Avalanche Current L = 0.1 mH		I _{AS}	80	
Single Avalanche Energy ^a	L = U.1 IIIH	E _{AS}	320	mJ
Maximum Dawar Dissination 8	T _C = 25 °C	В	375 ^b	14/
Maximum Power Dissipation ^a	T _C = 125 °C	P _D	125 ^b	W
Operating Junction and Storage Temperature Ra	T _J , T _{stq}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)	R _{thJC}	0.4	C/VV		

Notes

- a. Duty cycle ≤ 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).
- d. Package limited.

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			"		<u> </u>		
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.2	-	2.5	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	150	μA	
		V _{DS} = 40 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	120	-	-	Α	
Drain Source On State Registance 3	В	V _{GS} = 10 V, I _D = 30 A	-	0.00127	0.00160	Ω	
Drain-Source On-State Resistance a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$	-	0.00152	0.00190		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A	-	174	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz	-	11 155	-	pF	
Output Capacitance	Coss		-	7410	-		
Reverse Transfer Capacitance	C _{rss}		-	880	-		
Total Gate Charge c	Q_g		-	150	230	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	32	-		
Gate-Drain Charge ^c	Q_{gd}		-	11	-		
Gate Resistance	R_g	f = 1 MHz	0.32	1.6	3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	16	32	ns	
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, R_L = 5 \Omega$	-	20	40		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	65	100		
Fall Time ^c	t _f		-	17	35		
Drain-Source Body Diode Ratings ar	nd Characteris	stics ^b (T _C = 25 °C)					
Pulsed Current (t = 100 μs)	I _{SM}		-	-	300	Α	
Forward Voltage ^a	V_{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.8	1.5	V	
Reverse Recovery Time	t _{rr}		-	135	203	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 41 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	5	10	Α	
Reverse Recovery Charge	Q _{rr}	7		0.340	0.510	μC	

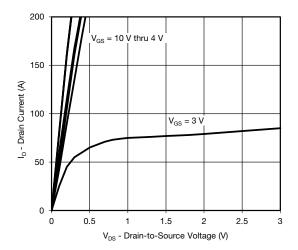
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

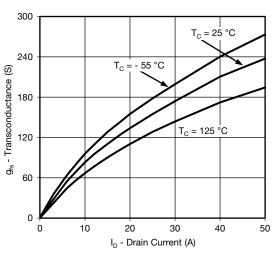
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



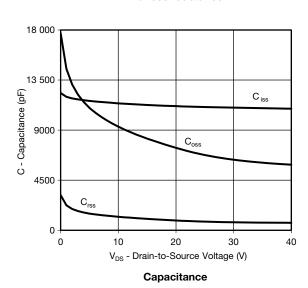
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

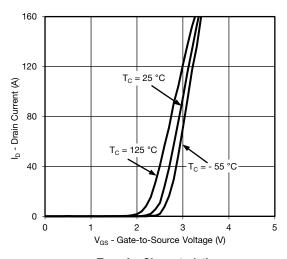


Output Characteristics

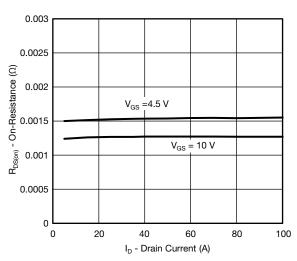


Transconductance

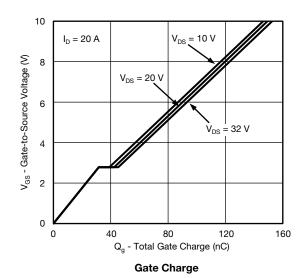




Transfer Characteristics

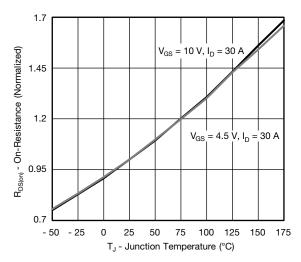


On-Resistance vs. Drain Current

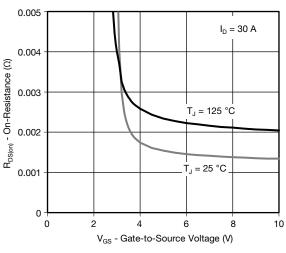




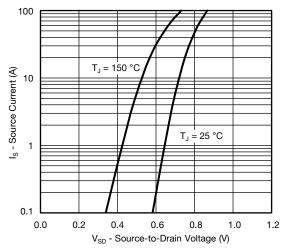
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



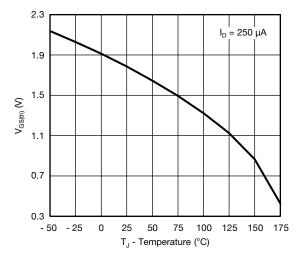
On-Resistance vs. Junction Temperature



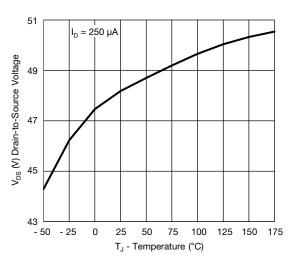
On-Resistance vs. Gate-to-Source Voltage



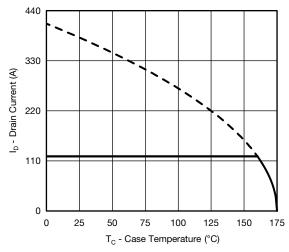
Source Drain Diode Forward Voltage



Threshold Voltage



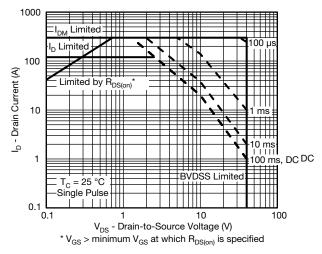
Drain Source Breakdown vs. Junction Temperature

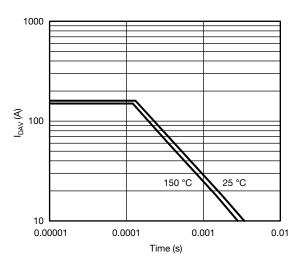


Current De-rating



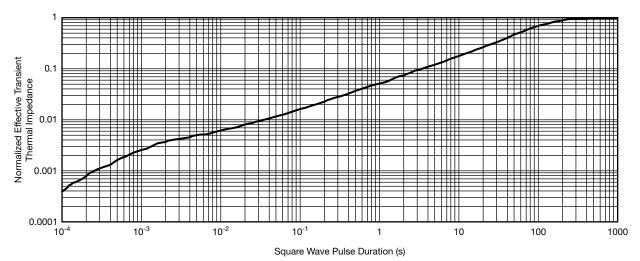
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)





Safe Operating Area

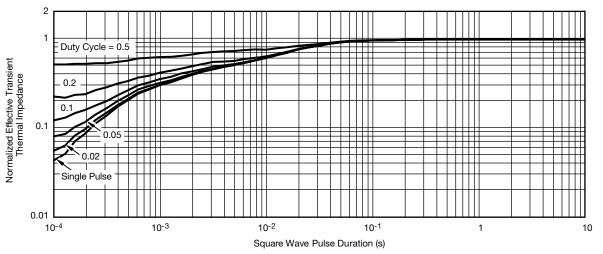
Single Pulse Avalanche Current Capability vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?66984.



TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



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- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

	INCHES		MILLIMETERS			
DIM.		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	=	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
е		0.100) BSC	2.54 BSC		
K		0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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